

LCP1521S/LCP152DEE

ASD (Application Specific Devices) Programmable transient voltage suppressor for SLIC protection

Features

- Dual programmable transient suppressor
- Wide negative firing voltage range: V_{MGL} = -150 V max.
- Low dynamic switching voltages: V_{FP} and V_{DGL}
- Low gate triggering current: I_{GT} = 5 mA max
- Peak pulse current: $I_{PP} = 30 \text{ A} (10/1000 \text{ µs})$
- Holding current: I_H = 150 mA min
- Low space consuming package

Description

These devices have been especially designed to protect new high voltage, as well as classical SLICs, against transient overvoltages.

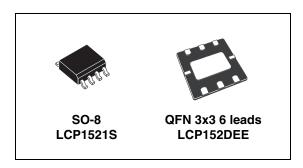
Positive overvoltages are clamped by 2 diodes. Negative surges are suppressed by 2 thyristors, their breakdown voltage being referenced to -V_{BAT} through the gate.

These components present a very low gate triggering current (I_{GT}) in order to reduce the current consumption on printed circuit board during the firing phase.

Benefits

TRISILs™ are not subject to ageing and provide a fail safe mode in short circuit for a better level of protection. Trisils are used to ensure equipment meets various standards such as UL60950, IEC950 / CSA C22.2, UL1459 and FCC part 68. Trisils have UL94 V0 approved resin (Trisils are UL497B approved [file: E136224]).

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Order codes

Part Number	Marking
LCP1521S	CP152S
LCP1521SRL	CP152S
LCP152DEERL	LCP152

Figure 1. LCP1521S Functional diagram

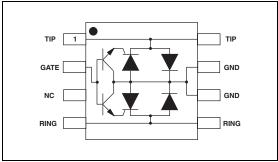
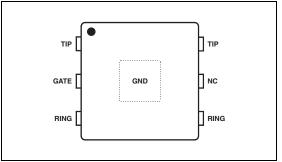


Figure 2. LCP152DEE Functional diagram



July 2006 Rev 5 1/11

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1 Characteristics

Table 1. Standards compliance

Standard	Peak surge voltage (V)	Voltage waveform	Required peak current (A)	Current waveform	Minimum serial resistor to meet standard (Ω)
GR-1089 Core First level	2500 1000	2/10 μs 10/1000 μs	500 100	2/10 μs 10/1000 μs	12 24
GR-1089 Core Second level	5000	2/10 μs	500	2/10 μs	24
GR-1089 Core Intra-building	1500	2/10 μs	100	2/10 μs	0
ITU-T-K20/K21	6000 1500	10/700 μs	150 37.5	5/310 µs	110 0
ITU-T-K20 (IEC 61000-4-2)	8000 15000	1/60 ns		ct discharge discharge	0
VDE0433	4000 2000	10/700 μs	100 50	5/310 µs	60 10
VDE0878	4000 2000	1.2/50 µs	100 50	1/20 µs	0 0
IEC61000-4-5	4000 4000	10/700 μs 1.2/50 μs	100 100	5/310 μs 8/20 μs	60 0
FCC Part 68, lightning surge type A	1500 800	10/160 μs 10/560 μs	200 100	10/160 μs 10/560 μs	22.5 15
FCC Part 68, lightning surge type B	1000	9/720 μs	25	5/320 µs	0

Table 2. Thermal resistances

Symbol	Parai	Value	Unit	
Ъ	lunation to ambient	SO-8	120	° C / / /
R _{th(j-a)}	Junction to ambient	QFN	140	° C/W

LCP1521S/LCP152DEE Characteristics

Table 3. Electrical characteristics $(T_{amb} = 25^{\circ} C)$

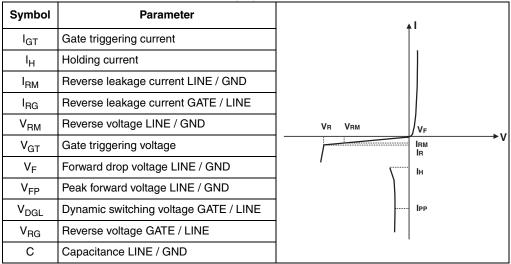


Table 4. Absolute ratings (T_{amb} = 25° C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
		10/1000 μs	30		
		8/20 µs	100)	
		10/560 μs	35		
I_{PP}	Peak pulse current	5/310 μs	40	Α	
		10/160 μs	50		
		1/20 µs	100		
		2/10 μs	150		
	Non repetitive surge peak on-state current	t = 20 ms	18	А	
I_{TSM}	(50Hz sinusoidal)	t = 200 ms	10		
	(con iz cinacoladi)	t = 1 s	7		
I_{GSM}	Maximum gate current (50Hz sinusoidal)	t = 10 ms	2	Α	
V_{MLG}	Maximum voltage LINE/GND	-40° C < Tamb < +85° C	-150	V	
V _{MGL}	Maximum voltage GATE/LINE	-40° C < Tamb < +85° C	-150	V	
T _{stg}	Storage temperature range		-55 to +150	° C	
Tj	Maximum junction temperature	150	C		
TL	Maximum lead temperature for soldering du	260	° C		

Table 5. Repetitive peak pulse current

Symbol	Definition	Example	% IPP ^
t _r	Rise time (µs)	Pulse waveform	100
t _p	Pulse duration (μs)	10/1000 μ s: $t_r = 10 \ \mu$ s $t_p = 1000 \ \mu$ s	$0 \xrightarrow{t_r t_p} t$

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Characteristics LCP1521S/LCP152DEE

Table 6. Parameters related to the diode LINE / GND ($T_{amb} = 25^{\circ} C$)

Symbol		Max	Unit		
V _F	I _F = 5A		t = 500 μs	3	V
V _{FP} ⁽¹⁾	10/700 μs 1.2/50 μs 2/10 μs	1.5 kV 1.5 kV 2.5 kV	$R_S = 10 \Omega$ $R_S = 10 \Omega$ $R_S = 62 \Omega$	5 9 30	V

^{1.} See test circuit for V_{FP} (*Figure 4.*): R_S is the protection resistor located on the line card.

Table 7. Parameters related to the protection Thyristors ($T_{amb} = 25^{\circ}$ C, unless otherwise specified)

Symbol	Test conditions				Тур	Max	Unit
I _{GT}	V _{GND / LINE} = -	48 V			0.1	5	mA
I _H	$V_{GATE} = -48 V^{0}$	(1)			150		mA
V_{GT}	at I _{GT}					2.5	٧
I _{RG}	V _{RG} = -150 V V _{RG} = -150 V			$T_j = 25^{\circ} \text{ C}$ $T_j = 85^{\circ} \text{ C}$		5 50	μΑ
V _{DGL}	V _{GATE} = -48 V ⁰ 10/700 μs 1.2/50 μs 2/10 μs	1.5 kV 1.5 kV 2.5 kV	$R_S = 10 \Omega$ $R_S = 10 \Omega$ $R_S = 62 \Omega$	I _{PP} = 30 A I _{PP} = 30 A I _{PP} = 38 A		7 10 25	V

^{1.} see functional holding current (I_H) test circuit

Table 8. Parameters related to diode and protection Thyristors (Tamb = 25° C, unless otherwise specified)

Symbol	Test conditions	Тур	Max	Unit	
I _{RM}	V _{GATE / LINE} = -1 V V _{RM} = -150 V VG _{ATE / LINE} = -1 V V _{RM} = -150 V	$T_j = 25^{\circ} \text{ C}$ $T_j = 85^{\circ} \text{ C}$		5 50	μΑ
С	$V_R = 50 \text{ V bias}, V_{RMS} = 1 \text{ V}, F = 1 \text{ MHz}$ $V_R = 2 \text{ V bias}, V_{RMS} = 1 \text{ V}, F = 1 \text{ MHz}$		15 35		pF

 $^{2. \}quad \text{see test circuit for V}_{DG} \text{ The oscillations with a time duration lower than 50ns are not taken into account.} \\$

LCP1521S/LCP152DEE Characteristics

Figure 3. Functional Holding Current (I_H) test circuit: GO-NO GO test

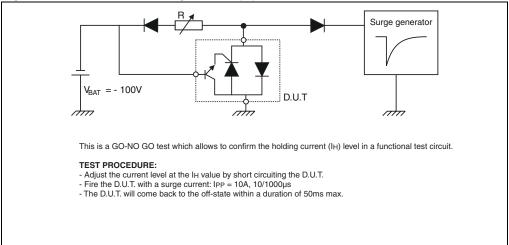
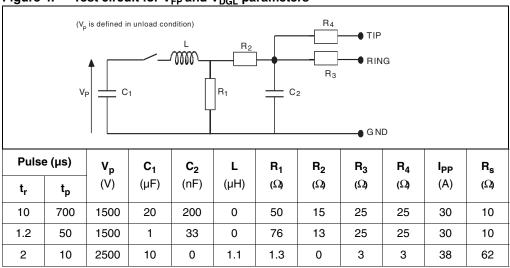


Figure 4. Test circuit for V_{FP} and V_{DGL} parameters



2 Technical information

Figure 5. LCP152 concept behavior

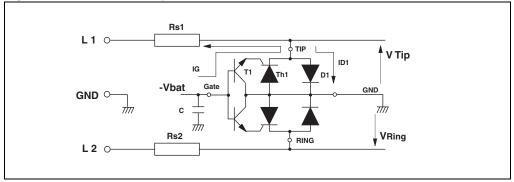


Figure 5. shows the classical protection circuit using the LCP152 crowbar concept. This topology has been developed to protect the new high voltage SLICs. It allows to program the negative firing threshold while the positive clamping value is fixed at GND.

When a negative surge occurs on one wire (L1 for example) a current IG flows through the base of the transistor T1 and then injects a current in the gate of the thyristor Th1. Th1 fires and all the surge current flows through the ground. After the surge when the current flowing through Th1 becomes less negative than the holding current IH, then Th1 switches off.

When a positive surge occurs on one wire (L1 for example) the diode D1 conducts and the surge current flows through the ground.

Figure 6. Example of PCB layout based on LCP152S protection

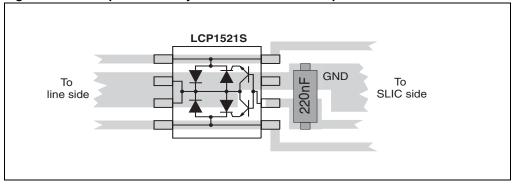


Figure 6. shows the classical PCB layout used to optimize line protection.

The capacitor C is used to speed up the crowbar structure firing during the fast surge edges.

This allows to minimize the dynamical breakover voltage at the SLIC Tip and Ring inputs during fast strikes. Note that this capacitor is generally present around the SLIC - Vbat pin.

So to be efficient it has to be as close as possible from the LCP152 Gate pin and from the reference ground track (or plan) (see *Figure 6*.). The optimized value for C is 220 nF.

The series resitors Rs1 and Rs2 designed in *Figure 5*. represent the fuse resistors or the PTC which are mandatory to withstand the power contact or the power induction tests

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imposed by the various country standards. Taking into account this fact the actual lightning surge current flowing through the LCP is equal to:

$$I_{surge} = V_{surge} / (R_g + R_s)$$

With:

V _{surge} = peak surge voltage imposed by the standard.

 R_{α} = series resistor of the surge generator

 R_s = series resistor of the line card (e.g. PTC)

e.g. For a line card with 30 Ω of series resistors which has to be qualified under GR1089 Core 1000V 10/1000 μ s surge, the actual current through the LCP152 is equal to:

$$I_{\text{surge}} = 1000 / (10 + 30) = 25 \text{ A}$$

The LCP152 is particularly optimized for the new telecom applications such as the fiber in the loop, the WLL, the remote central office. In this case, the operating voltages are smaller than in the classical system. This makes the high voltage SLICs particularly suitable.

The schematics of *Figure 7*. give the most frequent topology used for these applications.

Figure 7. Protection of high voltage SLIC

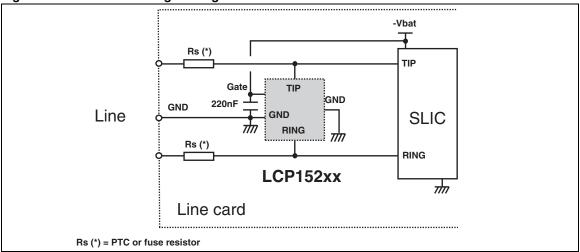
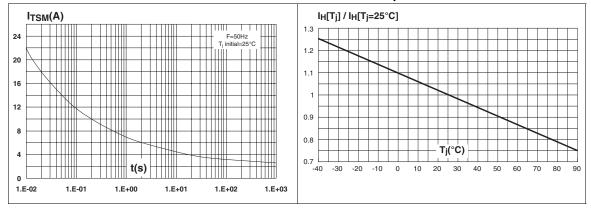


Figure 8. Surge peak current versus overload Figure 9. duration

Relative variation of holding current versus junction temperature



3 Package information

Table 9. SO-8 Dimensions

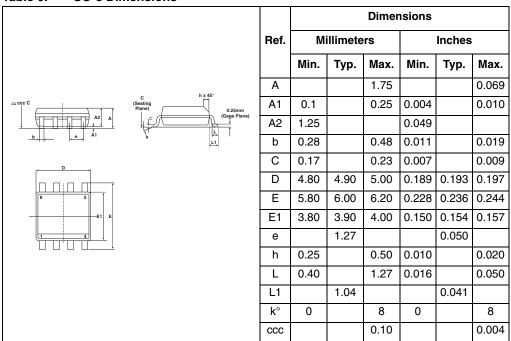
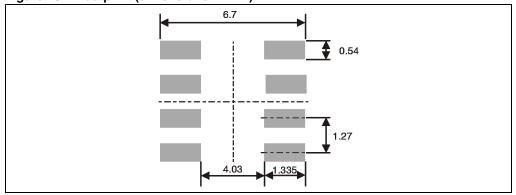


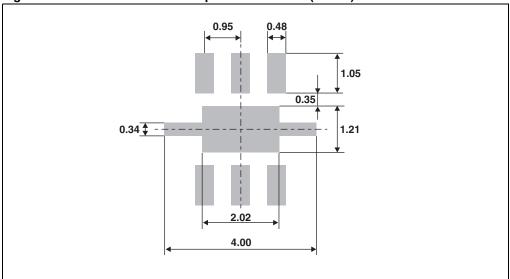
Figure 10. Footprint (dimensions in mm)



DIMENSIONS Millimeters REF. Inches Min. Max. Min. Max. Тур. Тур. Α 0.80 1 0.031 0.040 0.05 0.002 Α1 0 0 0.030 A2 0.65 0.75 0.026 0.787 АЗ 20 0.017 b 0.33 0.43 0.013 2.90 3.10 0.114 0.118 0.122 D2 0.083 1.92 2.12 0.076 Ε 2.90 0.114 0.118 0.122 3.10 E2 1.11 1.31 0.044 0.051 0.95 0.037 е L 0.008 0.20 0.45 0.018 L1 0.24 0.009 PROJECTION L2 0.13 0.005 Κ 0.20 0.008 0° 12° 0° 12° <

Table 10. QFN 3x3 6 Leads Package dimensions





4 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
LCP1521S	CP152S	SO-8	0.11 g	100	Tube
LCP1521SRL ⁽¹⁾	CP152S	30-0	0.11 g	2500	Tape and reel
LCP152DEERL ⁽¹⁾	LCP152	QFN 3x3 6L	0.022 g	3000	Tape and reel

^{1.} Preferred device

5 Revision history

Date	Revision	Description of Changes
Sep-2003	1A	First issue.
08-Dec-2004	2	1/ Page 2 table 3: Thermal resistances changed from 130° C/W (SO-8) to 120° C/W and from 170° C/W (QFN) to 140° C/W. 2/ SO-8 and QFN footprint dimensions added.
17-Feb-2005	3	Table 9 on page 4: correction of typo on capacitance unit.
03-May-2005	4	Table 5 on page 3: I _{TSM} value @ t= 1s from 4 A to 4.5 A.
07-Jul-2006	5	Replaced QFN package illustration on page 1. Reformatted document to current layout standard. Values of I _{TSM} modified in Table 4. SO-8 package dimensions updated in Table 9.

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